### **PDS Photosensor TDR Sections**

Bob Wilson Photosensor Working Group Meeting November 20, 2018

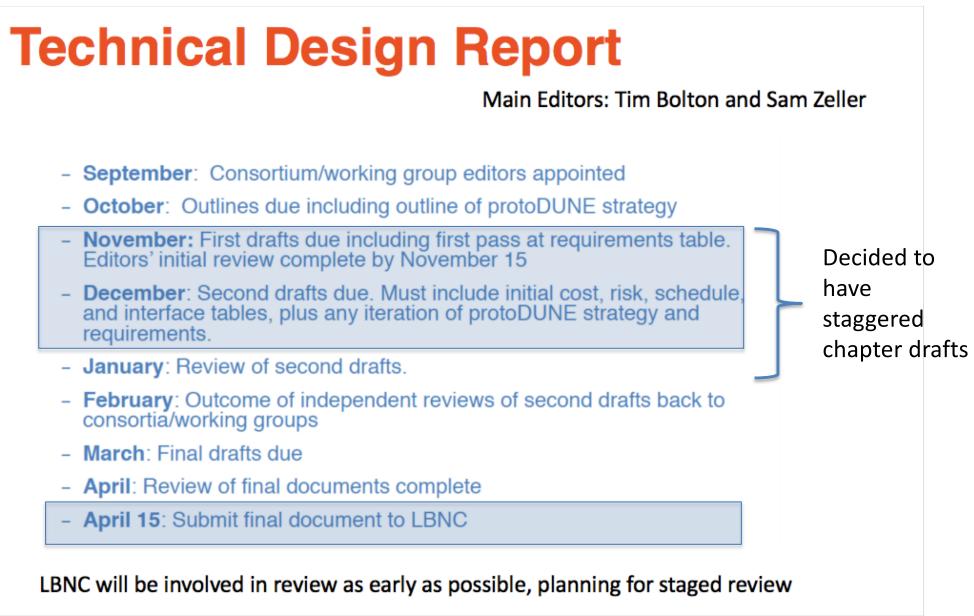




### **Eric J. – September 2018 collaboration meeting**

- SP-PD 30% Design Review: November 12-13 @ FNAL
- DAQ 30% Design Review: December 3-4 @ CERN (TBC)
- LBNC Meeting: December 7-9 @ CERN
- LBNF/DUNE-US DOE IPR: January 8-10 @ FNAL
- Collaboration Meeting: January 28-31, February 1 @ CERN
- RRB Meeting: March 14-15 @ FNAL
- LBNC Meeting: April 1-3 @ FNAL
- LBNC Meeting: July 31, August 1-2 @ FNAL
- RRB Meeting: September 19-20 @ FNAL
- LBNF/DUNE-US DOE CD-2/CD-3B Review: October @ FNAL

### Plenty of time, right ...



Consortium	1st draft	2nd draft	LBNC	
SP-HV	November 2, 2018	December 7, 2018	December 21, 2018	
SP-APA	November 2, 2018	-	-	
SP-DAQ	November 2, 2018	December 7, 2018	December 21, 2018	
SP-PDS	November 30, 2018	January 11, 2019	January 25, 2019	
SP-CISC	November 30, 2018	January 11, 2019	January 25, 2019	
ТС	November 30, 2018	January 11, 2019	January 25, 2019	
PHYSICS	November 30, 2018	January 11, 2019	January 25, 2019	

### • Overview

#### 1.1.2.2 Silicon Photosensors

In each photon collector concept, the final stage of converting a visible wavelength photon into an electrical signal is performed by a SiPM. The device must operate reliably for many years at LAr temperatures. Experience with a promising early candidate that failed in later batches, due to an unadvertised change in the fabrication process, emphasizes the importance of a multi-source approach with active engagement of potential vendors to develop a device expressly for cryogenic operation. Currently, there are ongoing investigations of MPPCs (multi-pixel photon counters) produced by Hamamatsu<sup>4</sup> (Japan) including a model specifically designed for cryogenic operation, and a device developed for operation in LAr by FBK<sup>5</sup> (Italy) in collaboration with the DarkSide experiment.

Change text to reflect MPPC as baseline with FBK option being vigorously pursued

### Photon Detector System Design

#### 4 1.3.2 Silicon Photosensors

pdate text to identify two candidates MPPC and FBK.

The SP module PDS uses a multi-step approach to scintillation light detection with final stage of conversion into electrical charge performed by silicon photomultipliers (SiPM). Robust photon detection efficiency, low operating voltages, small size and ruggedness make their use attractive the SP design where the photon detectors must be accommodated inside the APA frames. As implemented in ProtoDUNE-SP, there are twelve  $6 \times 6 \text{ mm}^2$  SiPMs per bar and 6 to 12 per ARAPUCA box. With this configuration, a 10kt SP module with 150 anode plane assemblies, each with 10 PD modules, would contain 18,000-36,000 (single or double-ended readout) SiPMs for the light guide designs and 10-20 times more for the higher granularity ARAPUCA design. This corresponds to approximately 1-13 m<sup>2</sup> of active SiPM surface area. The following summarizes the most salient guiding principles and requirements for this SiPM-based photodetection system. 17 The full suite of SiPM requirements (number of devices, spectral sensitivity, dynamic range, 18 triggering, zero-suppression threshold etc.) is determined by the physics goals and the pho-19 ton collection implementation. As discussed in Section 1.1.1, the requirements for SNB 20 neutrinos are not yet fully established however, R&D carried out to date indicates that de-21 vices from several vendors have the performance characteristics close to that needed for the 22 PDS (see Table 1.4). Nearly one thousand of several types of these devices are used in the 23

- $\frac{ProtoDUNE-SP}{PD^{12}}$ , which will provide an excellent test bed for evaluating and monitoring
- IDR had about 2 pages + ~1 page table
- Need to change the tense and tone to TDR level
- Maybe add more justification but not add more pages

24

Conten update

Zutshi

• 1.3.2 Baseline and options sensor characteristics

Table 1.4: Candidate Photosensors Characteristics.					
	Hamamatsu	sensL	KETEK	Advansid	
Series part $\#$	S13360	DS-MicroC	PM33	NUV-SiPMs	
Vbr range	48 V to 58 V	24.2 V to 24.7 V	27.5 V	24 V to 28 V	
Vop range	Vbr + 3 V	Vbr $+1$ V to $+3$ V	Vbr+2V to $+5$ V	Vbr $+2$ V to $+6$ V	
Temp. depen- dence	54 mV/K	21.5 mV/K	22 mV/K	26 mV/K	
Gain	$1.7 \times 10^{6}$	$3  imes 10^6$	$1.74 \times 10^{6}$	$3.6  imes 10^6$	
Pixel size	50 $\mu$ m	10 $\mu$ m to 50 $\mu$ m	15 $\mu$ m to 25 $\mu$ m	40 <i>µ</i> m	

- No point to details on devices we are not considering. Can mention them in the text, including cautionary tale of sensL.
- Add FBK DarkSide device details?
- Proceed or replace with a specifications table?
- Include ganging studies in this section, or in Electronics?

### • 1.4 Production and Assembly

#### 1.4.9 Photosensor Modules

<sup>3</sup> Depending on the photon collector technology selected, the <u>SiPM</u> analog signal will be ganged in <sup>4</sup> groups of 6-48 in close proximity to the sensors inside the LAr volume; both *passive* and *active* <sup>5</sup> ganging schemes are under consideration. Passive ganging (sensors in parallel) implemented with <sup>6</sup> traces on the <u>SiPM</u> mounting board (module) and has been implemented for <u>ProtoDUNE-SP</u>. The <sup>7</sup> <u>SiPMs</u> are mounted using a pick-and-place machine and standard surface mount device soldering <sup>8</sup> procedures. The ganged analog signals are then brought out via long cables (approximately 25 m) <sup>9</sup> for digitization outside the cryostat. <u>ProtoDUNE-SP</u> will provide essential operational experience <sup>10</sup> with a passive ganging board and signal transport provided by Teflon ethernet CAT6 cables. It is <sup>11</sup> already apparent that R&D is needed to optimize the connectors used to couple the cable to the <sup>12</sup> board; it is a priority to understand the mechanical stresses involved in the <u>SiPM-PCB-Connector</u> <sup>13</sup> system (with different CTEs) as it is cooled (or cycled) to cryogenic temperatures.

A basic level of active ganging locates summing circuitry on the board carrying the photosensors or

on a separate PCB also mounted on the PD module. A more complex scheme is being considered

that would include cold amplifiers and ADCs. This solution would provide more flexibility in the

<sup>17</sup> level of photosensor ganging and also obviate the need for carrying analog signals of long cables.

<sup>18</sup> Production of the board would follow standards practices but the complexity introduces concerns

with reliability and long-term stability issues related to cold electronics. Basic active ganging

<sup>20</sup> prototypes are under study with high priority but the design is not yet at a mature stage.

- Describe in the context of X-ARAPUCA
- Has a paragraph on ganging update to current status/efforts

Content Zut-

shi/Can

- Despite Thanksgiving... updates needed by this weekend!
  - Even that leaves just < one week for iterations and top level edits before first draft deadline - 30 November
- Not such a big challenge for the photosensors group compared to others